

List of Publications by Year in descending order

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13
papers

2,267
citations

758635

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1125271

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g-index

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13
docs citations

13
times ranked

4361
citing authors

#	ARTICLE	IF	CITATIONS
1	Band offsets and heterostructures of two-dimensional semiconductors. Applied Physics Letters, 2013, 102, .	1.5	1,361
2	Photoresponsive and Gas Sensing Field-Effect Transistors based on Multilayer WS ₂ Nanoflakes. Scientific Reports, 2014, 4, 5209.	1.6	377
3	Tunable Polarity Behavior and Self-Driven Photoswitching in p-WSe ₂ /n-WSe ₂ Heterojunctions. Small, 2015, 11, 5430-5438.	5.2	114
4	Various Structures of 2D Transition-Metal Dichalcogenides and Their Applications. Small Methods, 2018, 2, 1800094.	4.6	107
5	2D WS ₂ Based Asymmetric Schottky Photodetector with High Performance. Advanced Electronic Materials, 2021, 7, 2000964.	2.6	68
6	Self-Powered SnS _{1-x} Se _x Alloy/Silicon Heterojunction Photodetectors with High Sensitivity in a Wide Spectral Range. ACS Applied Materials & Interfaces, 2019, 11, 40222-40231.	4.0	58
7	Tunable Schottky Barrier at MoSe ₂ /Metal Interfaces with a Buffer Layer. Journal of Physical Chemistry C, 2017, 121, 9305-9311.	1.5	45
8	An asymmetric contact-induced self-powered 2D In ₂ S ₃ photodetector towards high-sensitivity and fast-response. Nanoscale, 2020, 12, 7196-7205.	2.8	44
9	Self-assembly In ₂ Se ₃ /SnSe ₂ heterostructure array with suppressed dark current and enhanced photosensitivity for weak signal. Science China Materials, 2020, 63, 1560-1569.	3.5	24
10	Anti-ambipolar behavior and photovoltaic effect in p-MoTe ₂ /n-InSe heterojunctions. Journal of Materials Chemistry C, 2021, 9, 10372-10380.	2.7	24
11	Near-Infrared, Self-Powered and Polarization-Sensitive Photodetector Based on GeSe ₂ /MoTe ₂ p-n Heterojunction. Advanced Materials Interfaces, 2022, 9, .	1.9	18
12	Tunable Polarity Behavior and High-Performance Photosensitive Characteristics in Schottky-Barrier Field-Effect Transistors Based on Multilayer WS ₂ . ACS Applied Materials & Interfaces, 2018, 10, 2745-2751.	4.0	17
13	High-Performance Broadband Photodetectors Based on n-MoS ₂ /p-Ge _{0.9} Sn _{0.1} Heterojunctions. ACS Applied Electronic Materials, 2021, 3, 3218-3225.	2.0	10